

ABSTRACT OF THE DISCLOSURE

In a driver built-in type p-Si TFT LCD, a channel width direction of a sampling TFT (6) constituting a part of a driver and having a large channel width is formed in a direction non-parallel with sides of a substrate or sides of pulse laser beams radiated for poly-crystallization of a-Si. For example, the channel width direction of the sampling TFT (6) is formed to have an angle of 45° relative to the substrate sides. Therefore, even when a dispersion in energy intensity is generated in an irradiated plane of pulse laser beams radiated to a-Si in a poly-crystallization process and a defective crystallized region [R] is formed on a p-Si film (13) in a direction corresponding to the dispersion, the defective crystallized region [R] extends across a part of each TFT (6). Formation of only a specified TFT (6) in the defective crystallized region [R] and occurrence of a difference in characteristics between the specified TFT and another TFT (6) are prevented. Consequently, generation of a low display-quality portion on a specified column on LCD and deterioration of display quality of the entire LCD are prevented.